

## GENERAL PURPOSE 100 mW GaAs MMIC AMPLIFIER, 0.8 - 3.8 GHz

### Typical Applications

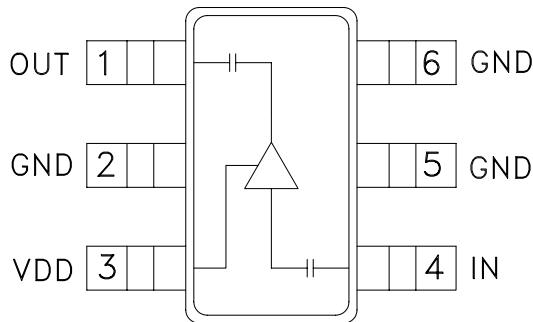
Broadband or Narrow Band Applications:

- Cellular/PCS/3G
- Fixed Wireless & Telematics
- Cable Modem Termination Systems
- WLAN, Bluetooth & RFID

### Features

- Gain: 18 dB
- P1dB Output Power: +17 dBm@ +5V
- Single Supply: +3V or +5V
- No External Components
- Integrated DC Blocks
- Ultra Small Package: SOT26

### Functional Diagram



### General Description

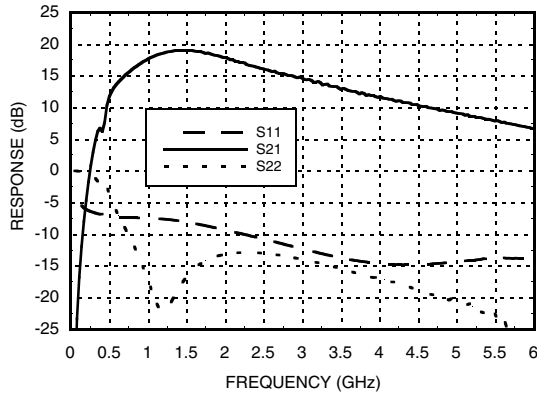
The HMC308 is a low cost MESFET MMIC amplifier that operates from a single +3 to +5V supply from 0.8 to 3.8 GHz. The surface mount SOT26 amplifier can be used as a broadband amplifier stage or used with external matching for optimized narrow band applications. With Vdd biased at +5V, the HMC308 offers 18 dB of gain and +20 dBm of saturated output power while requiring only 53 mA of current. This amplifier is ideal as a driver amplifier for transmitters or for use as a local oscillator (LO) amplifier to increase drive levels for passive mixers. The amplifier occupies 0.014 in<sup>2</sup> (9 mm<sup>2</sup>), making it ideal for compact radio designs.

### Electrical Specifications, T<sub>a</sub> = +25° C, as a function of Vdd

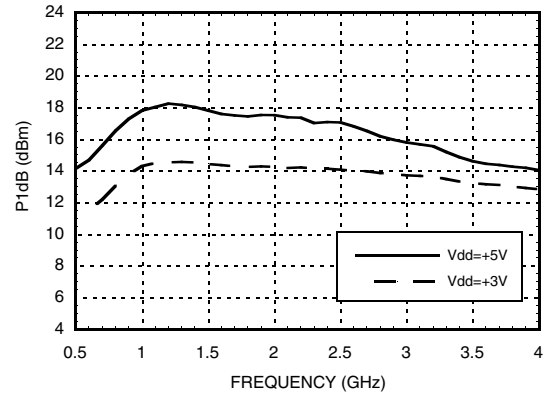
Parameter	Vdd = +3V			Vdd = +5V			Vdd = +5V			Vdd = +5V			Units
	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	
Frequency Range	2.3 - 2.7			0.8 - 2.3			2.3 - 2.7			2.7 - 3.8			GHz
Gain	13	15.5		14	18		13	16		10	13		dB
Gain Variation over Temperature		0.025	0.035		0.025	0.035		0.025	0.035		0.025	0.035	dB/°C
Input Return Loss		11			8			11			13		dB
Output Return Loss		17			13			12			13		dB
Output Power for 1 dB Compression (P1dB)	12	14		14	17		13.5	16.5		12	15		dBm
Saturated Output Power (Psat)		17			20			19.5			17		dBm
Output Third Order Intercept (IP3)	23	26		27	30		26	29		24	27		dBm
Noise Figure		7			7.5			7			7		dB
Supply Current (Idd)		50			53			53			53		mA

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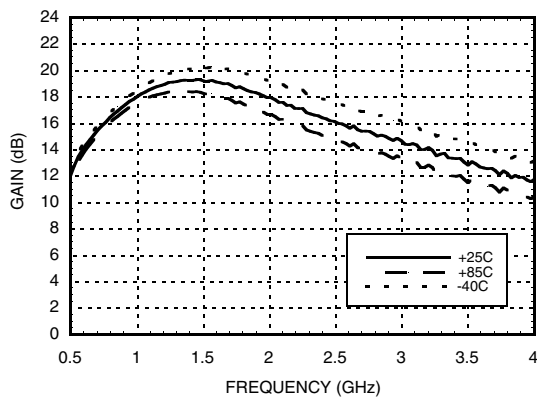
**Broadband Gain  
& Return Loss @ Vdd = +5V**



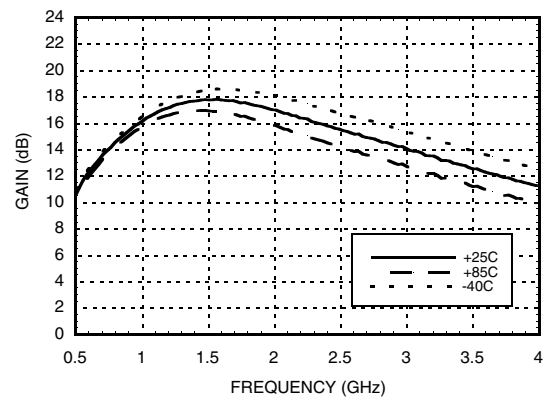
**P1dB vs. Vdd Bias**



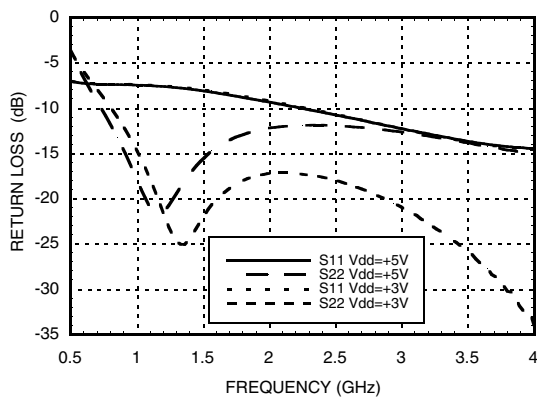
**Gain vs. Temperature @ Vdd = +5V**



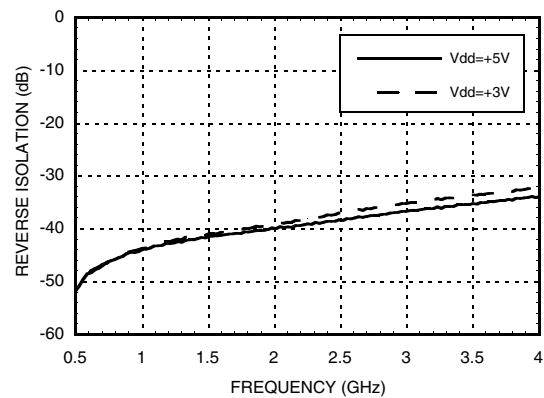
**Gain vs. Temperature @ Vdd = +3V**



**Input & Output  
Return Loss vs. Vdd Bias**

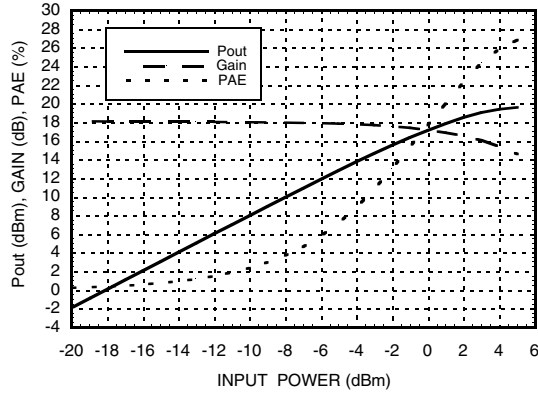


**Reverse Isolation vs. Vdd Bias**

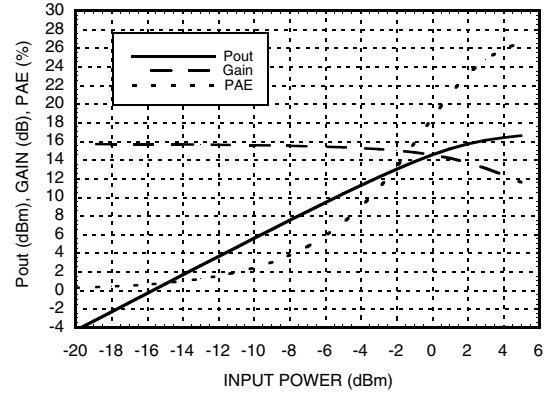


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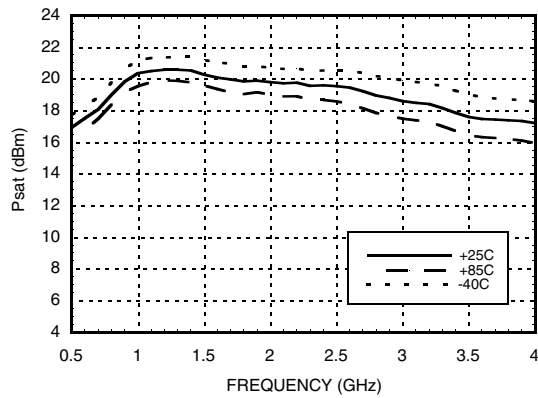
**Power Compression**  
@ 2.0 GHz, Vdd = +5V



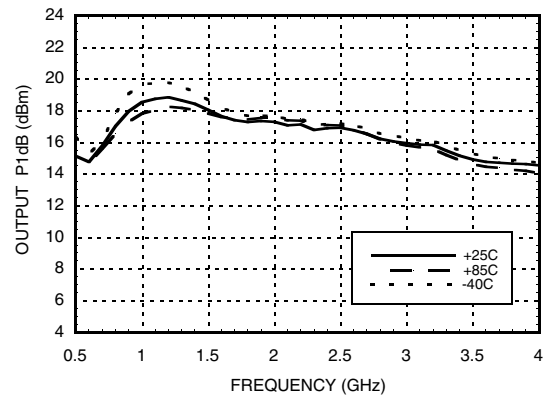
**Power Compression**  
@ 2.5 GHz, Vdd = +5V



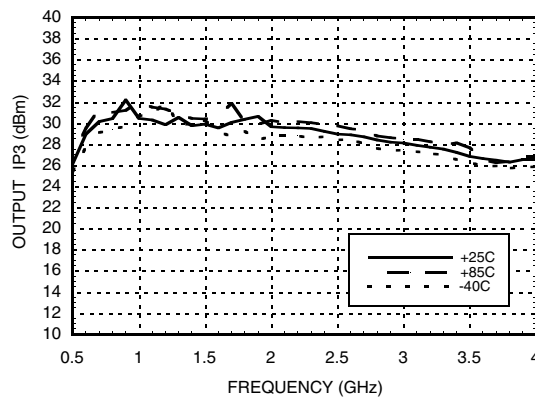
**Psat vs. Temperature @ Vdd = +5V**



**P1dB vs. Temperature @ Vdd = +5V**

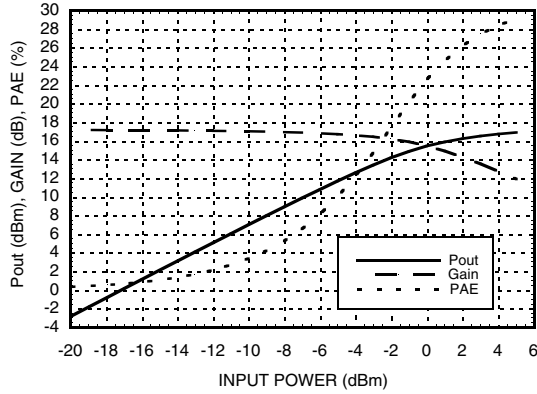


**Output IP3**  
vs. Temperature @ Vdd = +5V

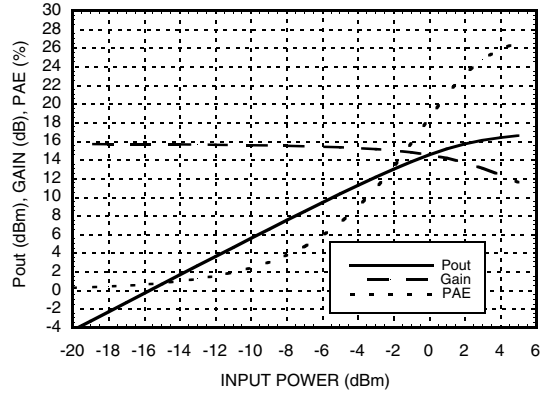


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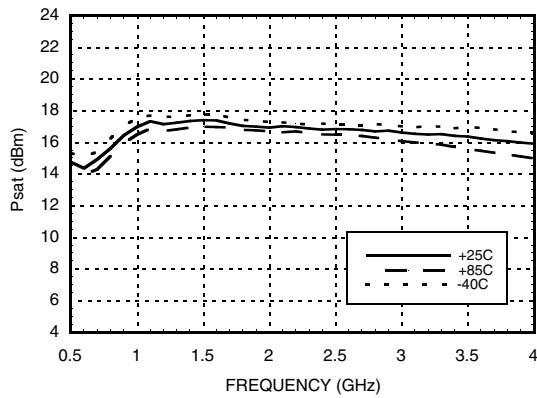
**Power Compression  
@ 2.0 GHz, Vdd = +3V**



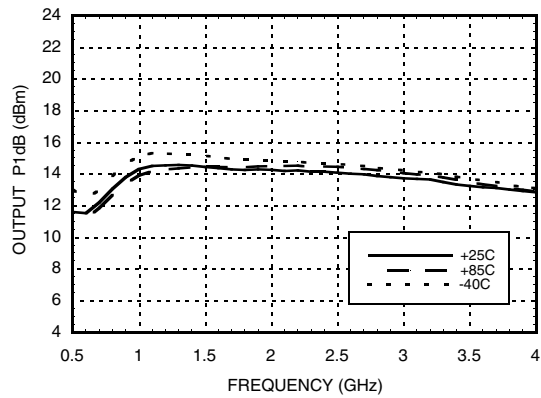
**Power Compression  
@ 2.5 GHz, Vdd = +3V**



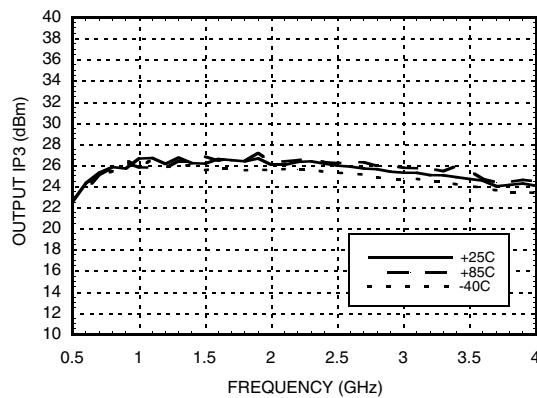
**Psat vs. Temperature @ Vdd = +3V**



**P1dB vs. Temperature @ Vdd = +3V**



**Output IP3  
vs. Temperature @ Vdd = +3V**



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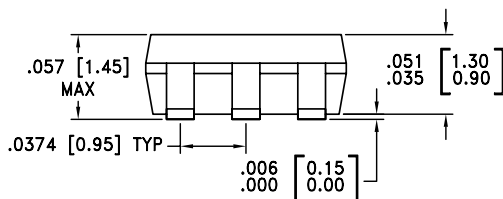
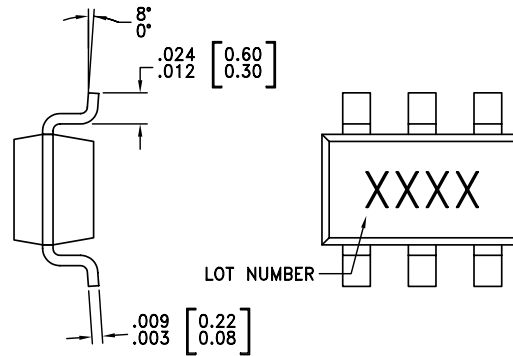
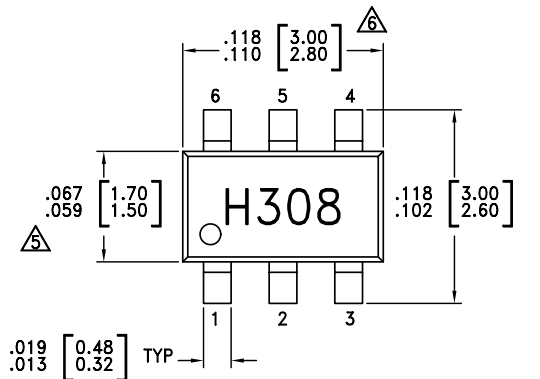
### Absolute Maximum Ratings

Drain Bias Voltage (Vdd)	+7.0 Vdc
RF Input Power (RFIn)(Vdd = +5.0 Vdc)	+10 dBm
Channel Temperature	150 °C
Continuous Pdiss (T = 85 °C) (derate 6.25 mW/°C above 85 °C)	0.406 W
Thermal Resistance (channel to lead)	160 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85 °C

### Typical Supply Current vs. Vdd

Vdd (Vdc)	Idd (mA)
+2.5	49
+3.0	50
+3.5	51
+4.5	50
+5.0	53
+5.5	54

### Outline Drawing

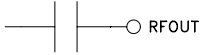

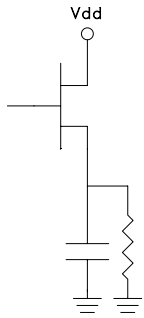
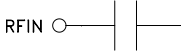


NOTES:

1. PACKAGE BODY MATERIAL: LOW STRESS INJECTION MOLDED PLASTIC SILICA AND SILICON IMPREGNATED.
2. LEADFRAME MATERIAL: COPPER ALLOY
3. LEADFRAME PLATING: Sn/Pb SOLDER
4. DIMENSIONS ARE IN INCHES [MILLIMETERS].
5. DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.15mm PER SIDE.
6. DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.25mm PER SIDE.
7. ALL GROUND LEADS MUST BE SOLDERED TO PCB RF GROUND.

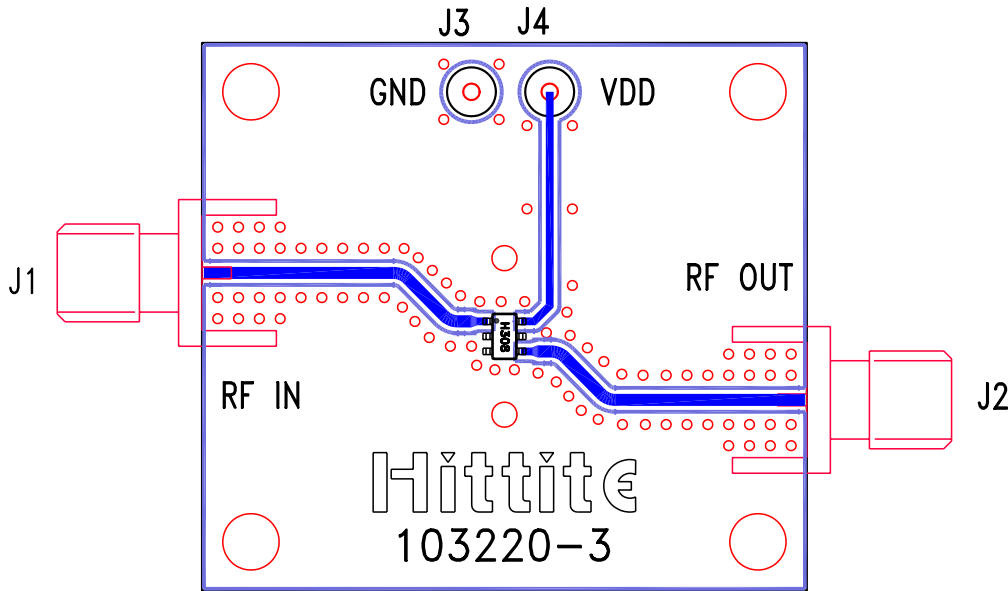
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### Pin Descriptions

Pin Number	Function	Description	Interface Schematic
1	RF OUT	This pin is AC coupled and matched to 50 Ohms.	
2, 5, 6	GND	These pins must be connected to RF/DC ground.	
3	Vdd	Power supply voltage.	
4	RF IN	This pin is AC coupled and matched to 50 Ohms.	

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### Evaluation PCB



### List of Material

Item	Description
J1, J2	PC Mount SMA Connector
J3, J4	DC Pins
U1	HMC308 Amplifier
PCB*	103220 Evaluation Board
*Circuit Board Material: Roger 4350	

The circuit board used in the final application should use RF circuit design techniques. Signal lines should have 50 ohm impedance while the package ground leads should be connected directly to the ground plane similar to that shown. A sufficient number of VIA holes should be used to connect the top and bottom ground planes. The evaluation circuit board shown is available from Hittite upon request.

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**Notes:**